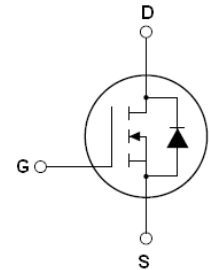


Main Product Characteristics

V_{DS}	650V
$R_{DS(ON)}$	300m Ω (Typ) @ $V_{GS}=10\text{ V}$
I_D	11.5A



TO-220F



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The SSFU6511 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0\text{V}$)	V_{DS}	650	V
Gate-Source Voltage ($V_{DS}=0\text{V}$), AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Continuous Drain Current at $T_C=25^\circ\text{C}$	$I_D (DC)$	11.5	A
Continuous Drain Current at $T_C=100^\circ\text{C}$	$I_D (DC)$	7	A
Pulsed Drain Current ¹	$I_{DM (pluse)}$	46	A
Maximum Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	32.6	W
Power Dissipation-Derate Above 25°C		0.26	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ²	E_{AS}	144	mJ
Avalanche Current ¹	I_{AR}	6	A
Repetitive Avalanche Energy t_{AR} Limited by T_{jmax} ¹	E_{AR}	0.5	mJ
Drain Source Voltage Slope, $V_{DS} \leq 480\text{ V}$,	dv/dt	50	V/nS
Reverse Diode dv/dt , $V_{DS} \leq 480\text{ V}$, $I_{SD} < I_D$	dv/dt	15	V/nS
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	$R_{\theta JC}$	3.83	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient (Maximum)	$R_{\theta JA}$	80	$^{\circ}C/W$

Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off States						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650	-	-	V
Zero Gate Voltage Drain Current($T_C=25^{\circ}C$)	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$	-	0.05	1	μA
Zero Gate Voltage Drain Current($T_C=125^{\circ}C$)	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$	-	-	100	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3	3.5	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=7A$	-	300	360	m Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$	-	870	-	pF
Output Capacitance	C_{oss}		-	54	-	pF
Reverse Transfer Capacitance	C_{rss}		-	1.8	-	pF
Total Gate Charge	Q_g	$V_{DS}=480V, I_D=11.5A,$ $V_{GS}=10V$	-	19	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	nC
Gate-Drain Charge	Q_{gd}		-	6.5	-	nC
Switching Times						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=380V, I_D=5.5A,$ $R_G=3\Omega, V_{GS}=10V$	-	11	-	nS
Turn-On Rise Time	t_r		-	8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	58	70	nS
Turn-Off Fall Time	t_f		-	9	14	nS
Source- Drain Diode Characteristics						
Source-Drain Current(Body Diode)	I_{SD}	$T_C=25^{\circ}C$	-	-	11.5	A
Pulsed Source-Drain Current(Body Diode)	I_{SDM}		-	-	46	A
Forward On Voltage	V_{SD}	$T_J=25^{\circ}C, I_{SD}=11.5A, V_{GS}=0V$	-	0.90	1.2	V
Reverse Recovery Time	t_{rr}	$T_J=25^{\circ}C, I_F=5.8A,$ $di/dt=100A/\mu S$	-	220	-	nS
Reverse Recovery Charge	Q_{rr}		-	2.2	-	μC
Peak Reverse Recovery Current	I_{rrm}		-	19	-	A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

2. $T_J=25^{\circ}C, V_{DD}=50V, V_G=10V, R_G=25\Omega.$

Typical Electrical and Thermal Characteristic Curves

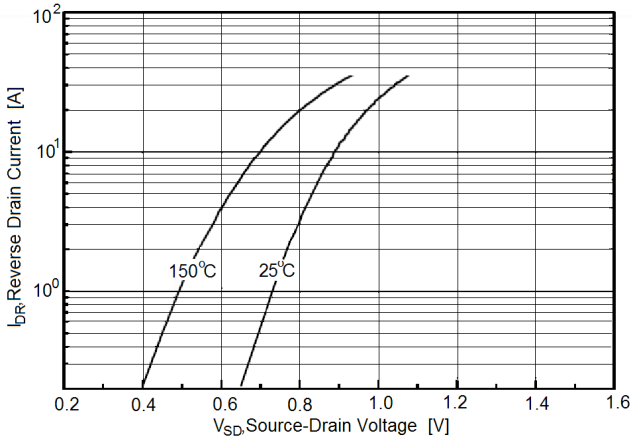


Figure 1. Source-Drain Diode Forward Voltage

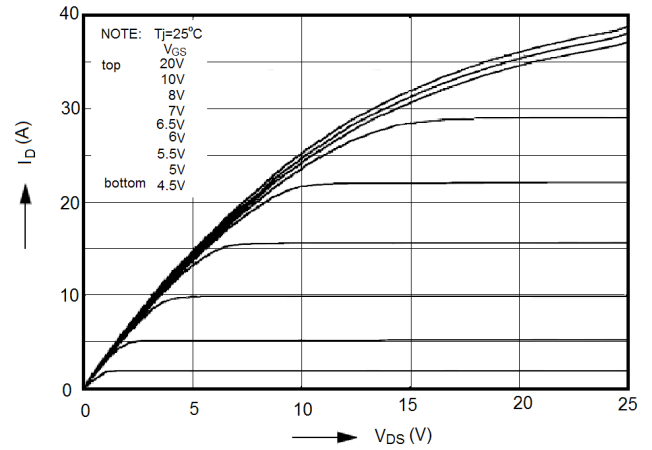


Figure 2. Output Characteristics

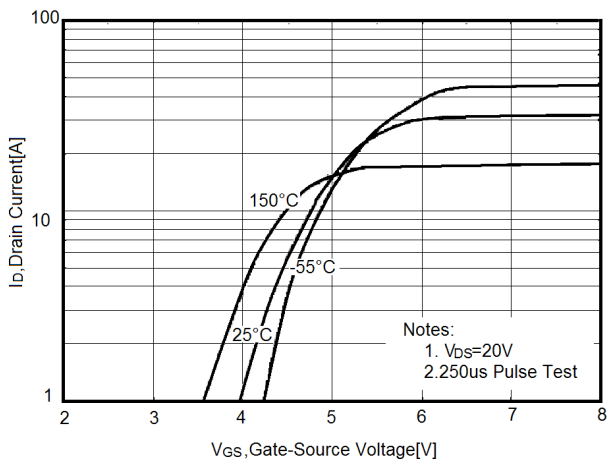


Figure 3. Transfer Characteristics

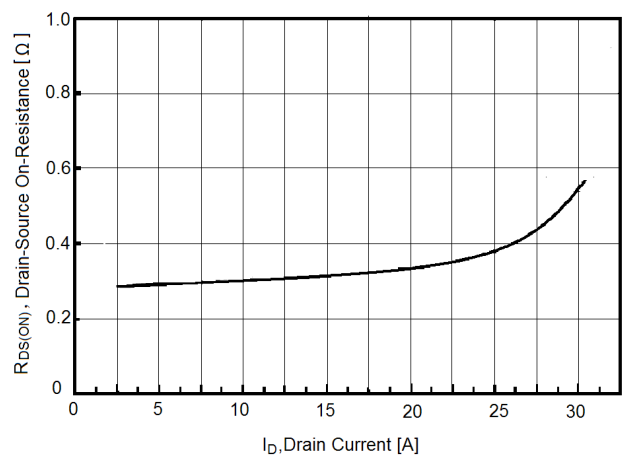


Figure 4. Static Drain-Source On Resistance

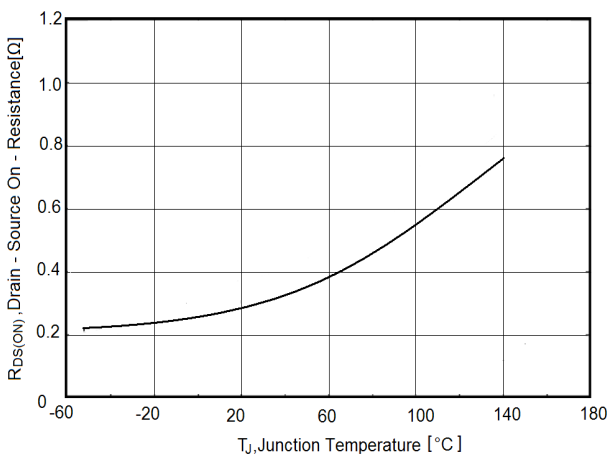


Figure 5. R_{DS(ON)} vs Junction Temperature

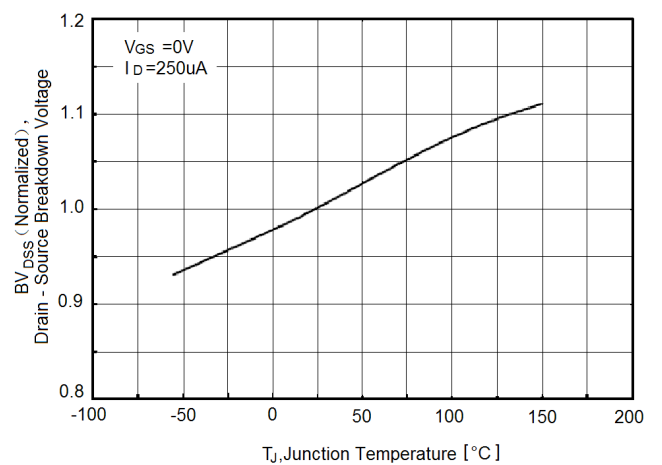


Figure 6. BV_{DSS} vs Junction Temperature

Typical Electrical and Thermal Characteristic Curves

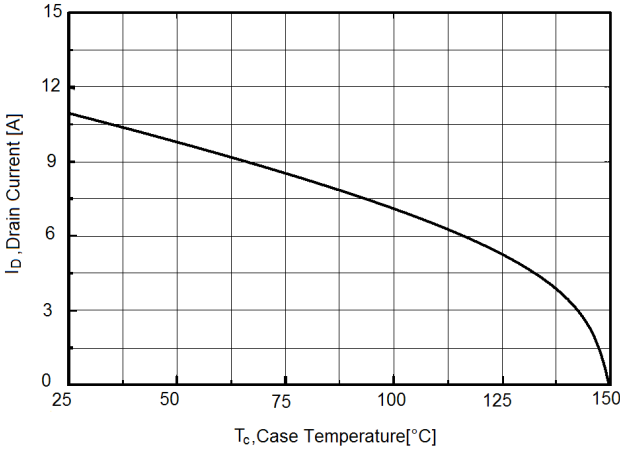


Figure 7. Maximum I_D vs Junction Temperature

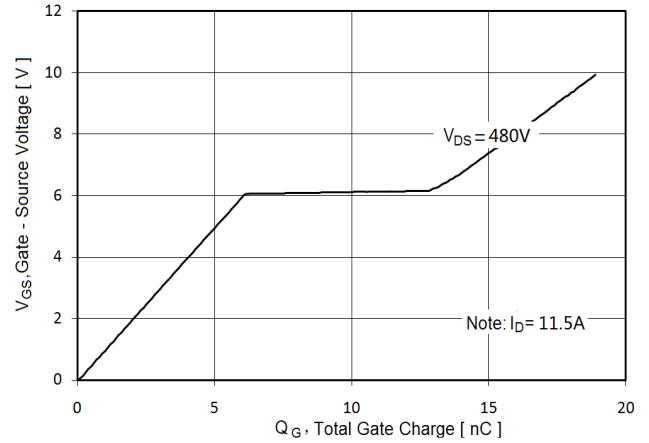


Figure 8. Gate Charge Waveforms

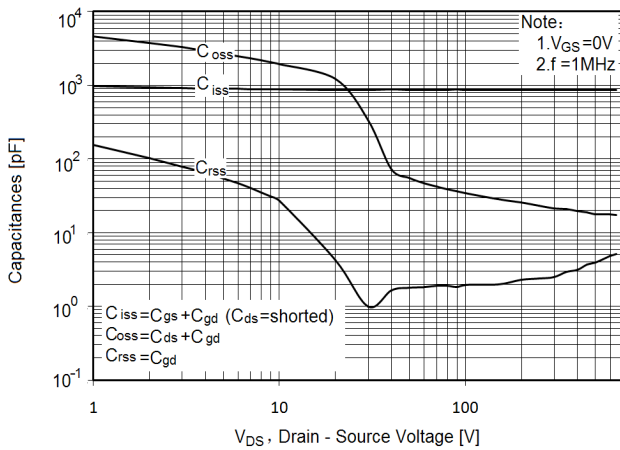


Figure 9. Capacitance

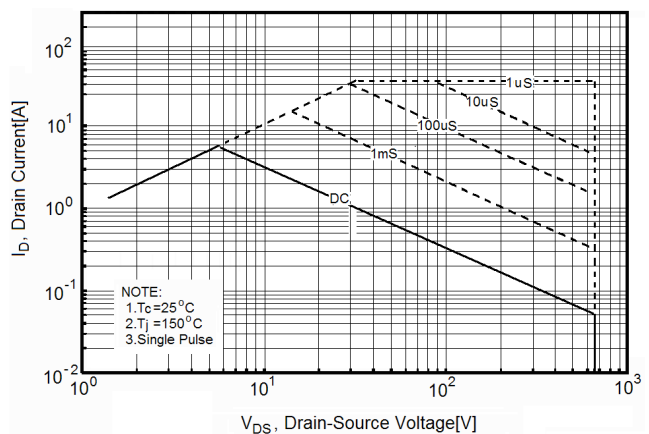


Figure 10. Safe Operating Area

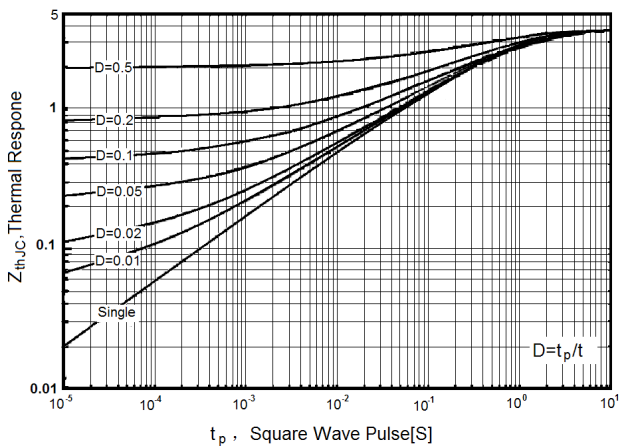


Figure 11. Transient Thermal Impedance

Test Circuit & Waveform

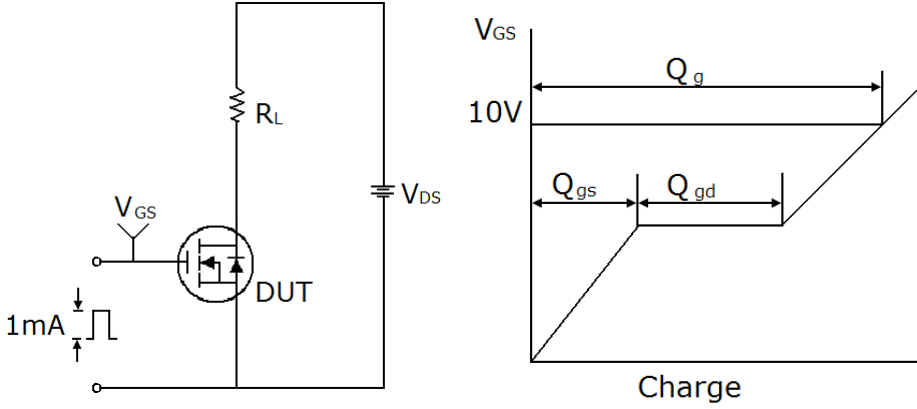


Figure 12. Gate Charge Test Circuit & Waveform

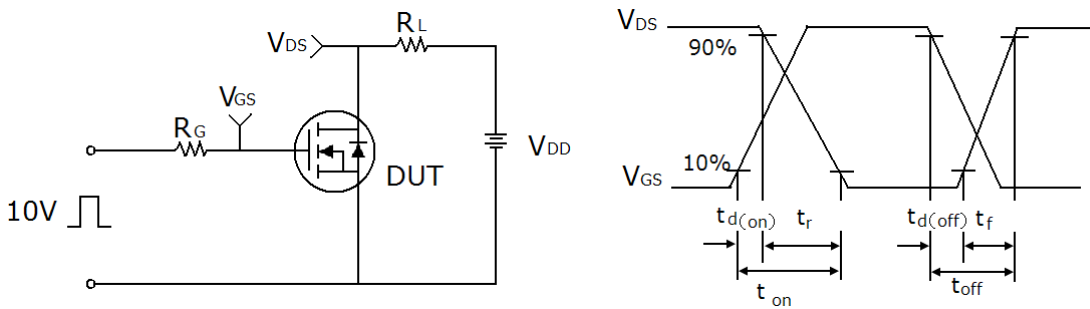


Figure 13. Switch Time Test Circuit & Waveforms

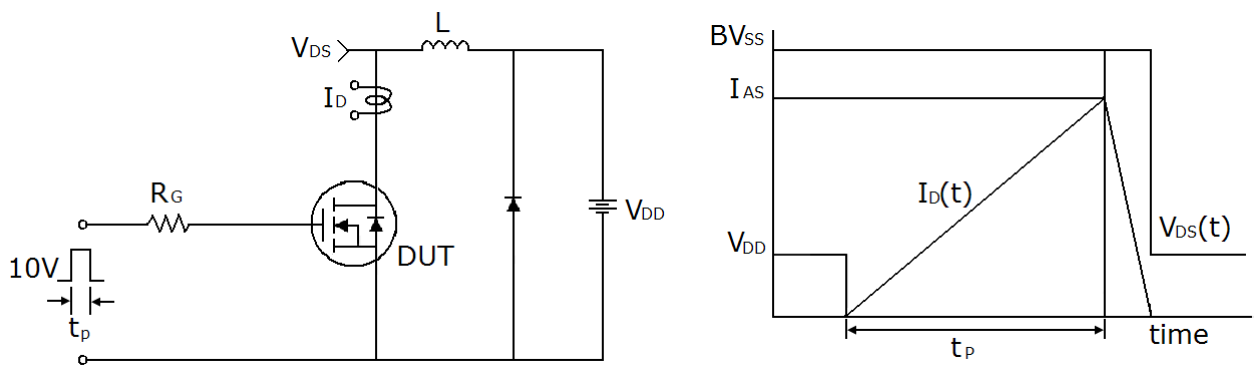
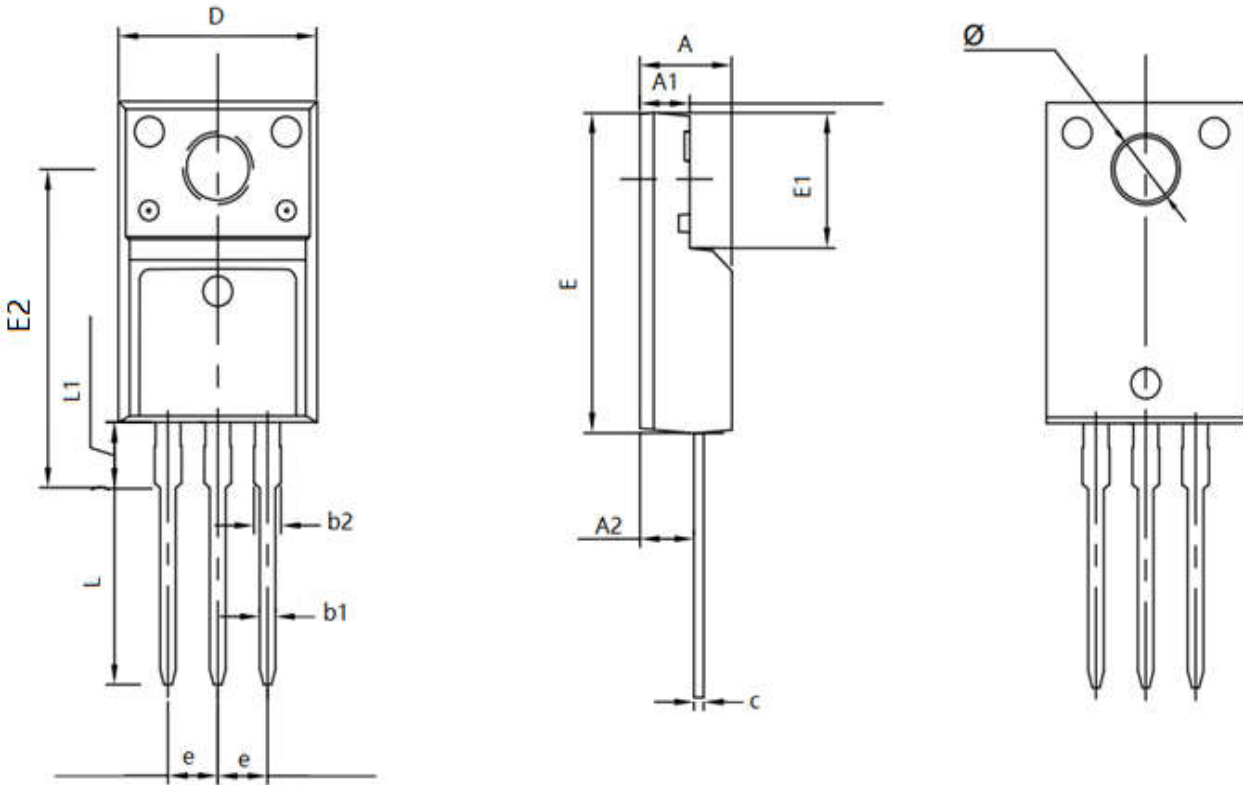


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline Dimensions

TO-220F



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.500	4.900	0.177	0.193
A1	2.340	2.740	0.092	0.108
A2	2.560	2.960	0.101	0.117
b1	0.700	0.900	0.028	0.035
b2	1.180	1.580	0.046	0.062
c	0.400	0.600	0.016	0.024
D	9.960	10.360	0.392	0.408
E	15.670	15.970	0.617	0.629
E1	6.500	6.900	0.256	0.272
E2	15.500	16.100	0.610	0.634
e	2.540 TYP		0.100 TYP	
Φ	3.080	3.280	0.121	0.129
L	12.640	13.240	0.498	0.521
L1	3.030	3.430	0.119	0.135